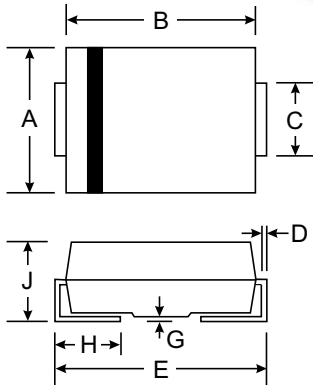


MURA105T3G - MURA160T3G

SURFACE MOUNT ULTRAFAST POWER RECTIFIERS DIODES



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SMA(DO-214AC)		
Dim	Min	Max
A	2.29	2.92
B	4.00	4.60
C	1.27	1.63
D	0.15	0.31
E	4.80	5.59
G	0.10	0.20
H	0.76	1.52
J	2.01	2.62
All Dimensions in mm		



VOLTAGE RANGE: 50 - 600V

CURRENT: 1.0 A

Features

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Voltage Drop, High Efficiency
- Low Power Loss
- Super-Fast Recovery Time
- Plastic Case Material has UL Flammability Classification Rating 94V-O

Mechanical Data

- Case: SMA/DO-214AC, Molded Plastic
- Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Marking: U4x = Specific Device Code
x = A for MURA105T3
= B for MURA110T3
= C for MURA115T3
= D for MURA120T3
= F for MURA130T3
= G for MURA140T3
= J for MURA160T3
- Weight: 0.064 grams (approx.)

Maximum Ratings and Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	MURA105	MURA110	MURA115	MURA120	MURA130	MURA140	MURA160	Unit
Maximum repetitive peak reverse voltage	V _{RRM}	50	100	150	200	300	400	600	V
Maximum RMS voltage	V _{RMS}	35	70	105	140	210	280	420	V
Maximum DC blocking voltage	V _{DC}	50	100	150	200	300	400	600	V
Maximum average forward rectified current at T _L =55°C	I _(AV)	1.0							A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	30.0							A
Maximum instantaneous forward voltage at 1.0A	V _F	0.95				1.25		1.7	V
Maximum DC reverse current T _A =25°C at rated DC blocking voltage T _A =100°C	I _R	5.0 50.0							μA
Maximum reverse recovery time (NOTE 1)	t _{rr}	35							ns
Typical junction capacitance (NOTE 2)	C _J	15.0							pF
Typical thermal resistance (NOTE 3)	R _{θJA}	60.0							°C/W
Operating junction and storage temperature range	T _J ,T _{STG}	-50 to +150							°C

Note: 1.Reverse recovery condition $I_F=0.5\text{A}$, $I_R=1.0\text{A}$, $I_{rr}=0.25\text{A}$
2.Measured at 1MHz and applied reverse voltage of 4.0V D.C.
3.P.C.B. mounted with 0.2x0.2" (5.0x5.0mm) copper pad areas

MURA105T3G - MURA160T3G

SURFACE MOUNT ULTRAFAST POWER RECTIFIERS DIODES

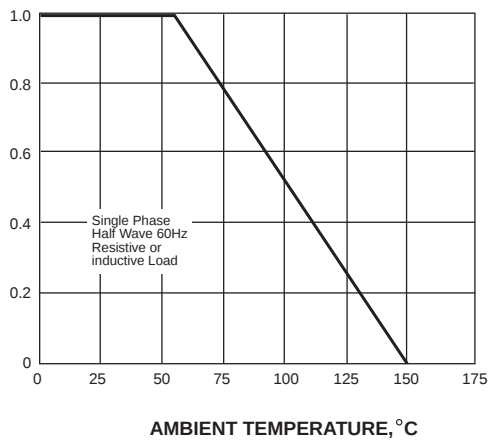


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RATINGS AND CHARACTERISTIC CURVES MURA105 THRU MURA160

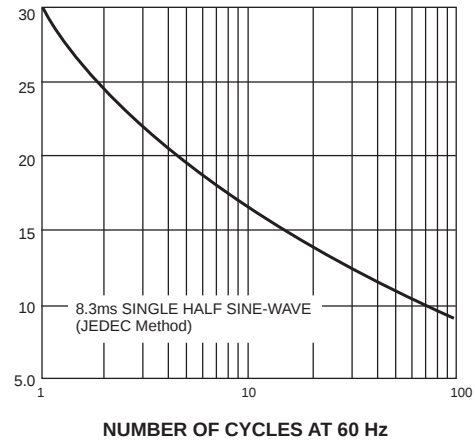
AVERAGE FORWARD RECTIFIED CURRENT,
AMPERES

FIG. 1- FORWARD CURRENT DERATING CURVE



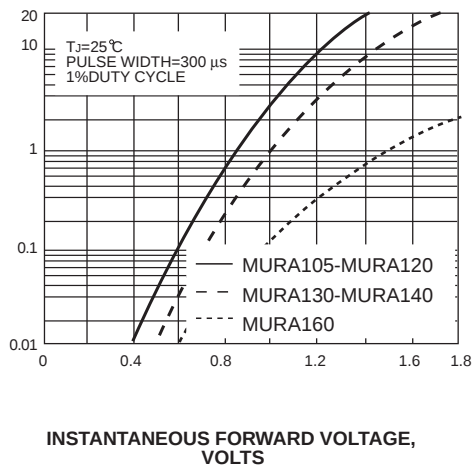
PEAK FORWARD SURGE CURRENT,
AMPERES

FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT



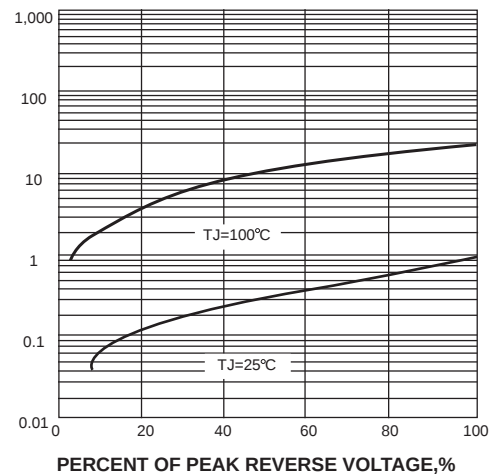
INSTANTANEOUS FORWARD CURRENT,AMPERES

FIG. 3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS



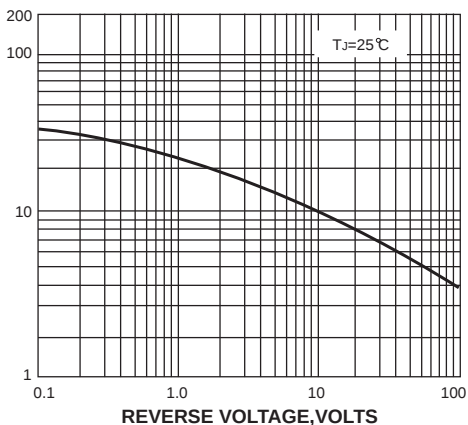
INSTANTANEOUS REVERSE CURRENT,
MICROAMPERES

FIG. 4-TYPICAL REVERSE CHARACTERISTICS



JUNCTION CAPACITANCE, pF

FIG. 5-TYPICAL JUNCTION CAPACITANCE



TRANSIENT THERMAL IMPEDANCE,
°C/W

FIG. 6-TYPICAL TRANSIENT THERMAL IMPEDANCE

